## 503125368 01/06/2015

## PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1 Stylesheet Version v1.2

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EPAS ID: PAT3171976

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

#### **CONVEYING PARTY DATA**

Name	Execution Date
Shih-Chieh Pu	12/30/2014
Ming-Tsung Lee	12/30/2014
Cheng-Hua Yang	12/30/2014
Nien-Chung Li	12/30/2014
Wen-Fang Lee	12/30/2014
Chih-Chung Wang	12/30/2014

#### **RECEIVING PARTY DATA**

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Street Address:	No.3, Li-Hsin Road 2, Science-Based Industrial Park
City:	Hsin-Chu City
State/Country:	TAIWAN

### **PROPERTY NUMBERS Total: 1**

Property Type	Number
Application Number:	14590957

#### **CORRESPONDENCE DATA**

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Email: Patent.admin.uspto.cr@naipo.com

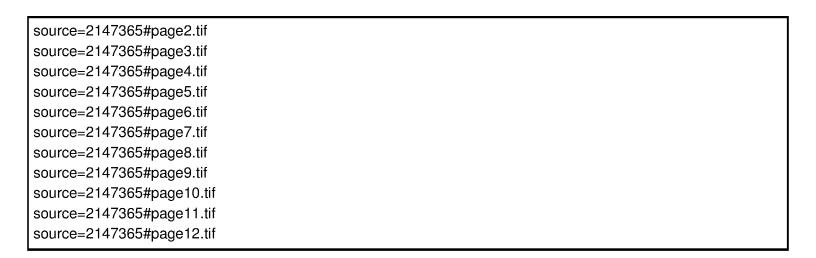
**Correspondent Name:** WINSTON HSU **Address Line 1:** P.O.BOX 506

Address Line 4: MERRIFIELD, VIRGINIA 22116

ATTORNEY DOCKET NUMBER:	NAUP2369USA
NAME OF SUBMITTER:	KATE YEH
SIGNATURE:	/KATE YEH/
DATE SIGNED:	01/06/2015

**Total Attachments: 12** source=2147365#page1.tif

PATENT 503125368 REEL: 034648 FRAME: 0413



## Title of Invention: HIGH VOLTAGE METAL-OXIDE-SEMICONDUCTOR TRANSISTOR DEVICE

As the below named inventor, I here This declaration is directed to:	by declare that:			
☑ The attached application, or				
☐ United States application nu	mber	filed c	n	, or
☐ PCT international application	n number	file	d on	
The above-identified application was	made or authorized to be	made by me.		
I believe that I am the original invent application.	or or an original joint inver	ntor of a claime	d invention in the	
I hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impr				
In consideration of the payment by	UNITED MICROELEC	CTRONICS	having a postal a	ddress of
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(referred to as "ASSIGNEE"below) to acknowledged, andfor other good ar		ar (\$ 1.00), the	receipt of which is	hereby
I hereby sell, assign and transfer to a the entire right, title and interest in a invention as above-identified applica invention by the above application of substitutes, or extensions thereof, ar	nd to any and all improver ition and, in and to, all Leti r any continuations, contin	nents which are ers Patent to b uation-in-part, e	e disclosed in the e obtained for said divisions, renewals	',
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representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have h	olication, said invention an ecessary or desirable to ca	d said Letters F erry out the prop	Patent and said poses thereof.	e of signing)
Note: An application data sheet (PT0 inventive entity, must accompany thi				

Page 1 of 12

Inventor: Shih-Chieh Pu Date: DEC 3 0 2014

Signature: Shih-Chieh Pa

Page 2 of 12

NPO#NAU-P2369-USA:0 CUST#UMCD-2014-0411

F#NPO-P0002E-US1201 DSC0-103U009473

### Title of Invention:

## HIGH VOLTAGE METAL-OXIDE-SEMICONDUCTOR TRANSISTOR DEVICE

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further covenant that ASSIGNEE wand documents relating to said inver known and accessible to I and will te related thereto and will promptly exe	ntion and said Letters Patent and lestify as to the same in any interfe	legal equivalents as may be rence, litigation proceeding	ts
representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be ne N WINTNESS WHEREOF, I have he	plication, said invention and said Lecessary or desirable to carry out	etters Patent and said the proposes thereof.	f signing)
Note: An application data sheet (PTC nventive entity, must accompany this	D/SB/14 or equivalent), including of some second of the se	naming the entire	

Page

3 of 12

LEGAL NAME OF INVENTOR(ASSIGNOR)					
Inventor:	Ming-Tsung Lee	Date:	DEC 3 0 2014		
Signature:	Ming-Tsung	Lee			

Page 4 of 12

NPO#NAU-P2369-USA:0 CUST#UMCD-2014-0411

### **Title of Invention:**

## HIGH VOLTAGE METAL-OXIDE-SEMICONDUCTOR TRANSISTOR DEVICE

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I further covenant that ASSIGNEE wand documents relating to said inver known and accessible to I and will te related thereto and will promptly exe	ntion and said Letters Patent are estify as to the same in any inte	nd legal equivalents a erference, litigation pr	as may be
representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have h	olication, said invention and sai ecessary or desirable to carry o	id Letters Patent and out the proposes there	said
Note: An application data sheet (PT0 inventive entity, must accompany thi			

Page 5 of 12

NPO#NAU-P2369-USA:0 CUST#UMCD-2014-0411

LEGAL NAME OF INVENTOR(ASSIGNOR)

Inventor:

Cheng-Hua Yang

Date:

DEC 3 0 2014

Signature

ure: Chang-Hua Sang

Page 6 of 12

F#NPO-P0002E-US1201 DSC0-103U009473

NPO#NAU-P2369-USA:0

CUST#UMCD-2014-0411

### Title of Invention:

## HIGH VOLTAGE METAL-OXIDE-SEMICONDUCTOR TRANSISTOR DEVICE

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I hereby covenant that no assignment entered into which would conflict with	nt, sale, agreement or encumb on this assignment;	rance has been or will be n	nade or
I further covenant that ASSIGNEE wi and documents relating to said inven known and accessible to I and will te- related thereto and will promptly exec	tion and said Letters Patent ar stify as to the same in any inte	nd legal equivalents as may erference, litigation proceed	v be
representatives any and all papers, in maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have he	lication, said invention and sai cessary or desirable to carry o	id Letters Patent and said out the proposes thereof.	ate of signing)
Note: An application data sheet (PTC inventive entity, must accompany this			

Page 7 of 12

NPO#NAU-P2369-USA:0 CUST#UMCD-2014-0411

LEGAL NAME OF INVENTOR(ASSIGNOR)					
Inventor:	Nien-Chung Li	Date:	DEC 3 0 2014		
Signature:	Nien Umg Li				

NPO#NAU-P2369-USA:0 CUST#UMCD-2014-0411 Page 8 of 12

F#NPO-P0002E-US1201 DSC0-103U009473

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representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have he	olication, said invention and said L ecessary or desirable to carry out	Letters Patent and said the proposes thereof.	te of signing)
Note: An application data sheet (PTC inventive entity, must accompany this	D/SB/14 or equivalent), including a s form. Use this form for <u>each add</u>	naming the entire	

Page 9 of 12

NPO#NAU-P2369-USA:0 CUST#UMCD-2014-0411

LEGAL NAME OF INVENTOR(ASSIGNOR)								
Inventor:	Wen-Fang Lee	Date:	DEC 3 0 2014					
Signature:	Wen- jung Lol							

Page

10 of 12

F#NPO-P0002E-US1201 DSC0-103U009473

NPO#NAU-P2369-USA:0 CUST#UMCD-2014-0411

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NPO#NAU-P2369-USA:0 CUST#UMCD-2014-0411

LEGAL NAME OF INVENTOR(ASSIGNOR)								
Inventor:	Chih-Chung Wang	Date	e: DEC	3 0 2014				
Signature:	Chih-chung	Wang						
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Page 12 of 12

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**RECORDED: 01/06/2015** 

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